2SK3700

查询"2SK37000協加商 Field Effect Transistor Silicon N Channel MOS Type (π-MOSIV)

2SK3700

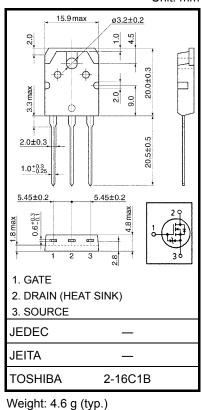
Switching Regulator Applications

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- Low drain-source ON resistance: $RDS(ON) = 2.0 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 4.5 \text{ S} (typ.)$
- Low leakage current: $I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 720 \ V)$
- Enhancement model: V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	900	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	900	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	5	А	
	Pulse (Note 1)	I _{DP}	15	~	
Drain power dissipation		PD	150	W	
Single pulse avalanche energy (Note 2)		E _{AS}	351	mJ	
Avalanche current		I _{AR}	5	А	
Repetitive avalanche energy (Note 3)		E _{AR}	15	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to150	°C	



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.833	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W	

Note 1: Ensure that the temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$ (initial), L = 25.7mH, R_G = 25 Ω , I_{AR} = 5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

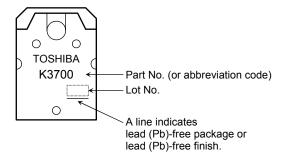
This transistor is an electrostatic-sensitive device. Please handle with caution.

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 25~V,~V_{DS}=0~V$			±10	μA
Gate-source breakdown voltage		V (BR) GSS	$I_{G} = \pm 10 \mu$ A, $V_{DS} = 0V$	±30	_	_	V
Drain cut-OFF current		I _{DSS}	$V_{DS} = 720 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		—	100	μA
Drain-source breakdown voltage		V (BR) DSS	$I_{G} = 10mA, V_{GS} = 0 V$	900	_		V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON	resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$	_	2.0	2.5	Ω
Forward transfer	Forward transfer admittance		$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 3 \text{ A}$	2.0	4.5	_	S
Input capacitance		C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	1150	_	pF
Reverse transfer capacitance		C _{rss}			20	_	
Output capacitance		C _{oss}		_	100	_	
Switching time	Rise time	tr	$V_{GS}^{10 \text{ V}} \downarrow_{DD} = 3 \text{ A} \\ 0 \text{ V} \downarrow_{O} \downarrow$		30		• ns
	Turn-ON time	t _{on}			70		
	Fall time	t _f			60		
	Turn-OFF time	t _{off}			170		
Total gate charge (gate-source plus gate-drain)		Qg			28		nC
Gate-source charge		Q _{gs}	V _{DD} ≒400 V, V _{GS} = 10 V, I _D = 5 A		17		
Gate-drain ("miller") charge		Q _{gd}		_	11	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	5	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	15	А
Forward voltage (diode)	V _{DSF}	$I_{DR} = 5 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V},$	_	900	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} /dt = 100 A/μs	_	5.4	_	μC

Marking



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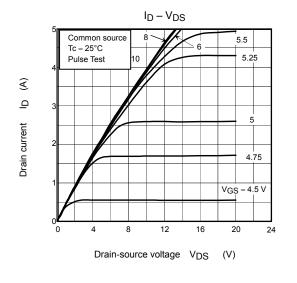
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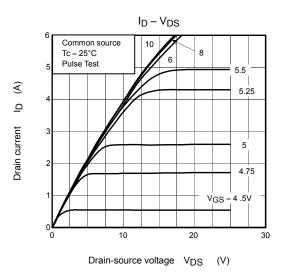
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Drain current

V_{DS} = 10 V

Pulse Test





 $I_D - V_{GS}$ Common source

Tc = -55°C

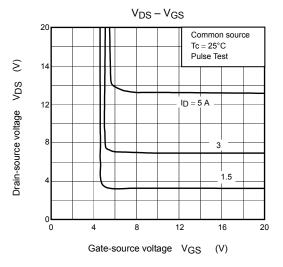
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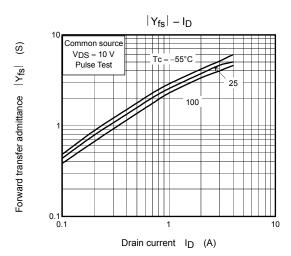
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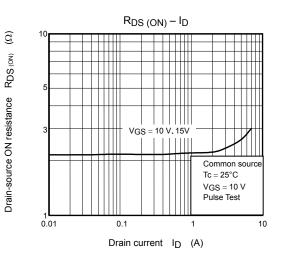
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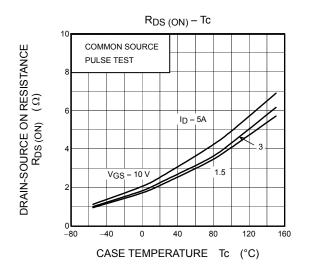
Gate-source voltage VGS

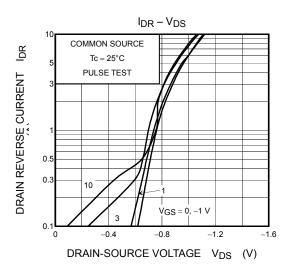


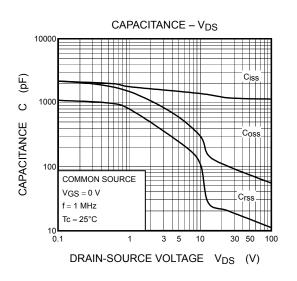
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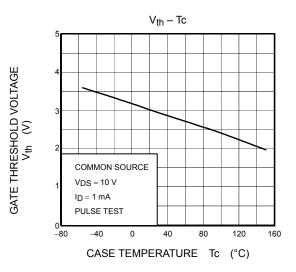
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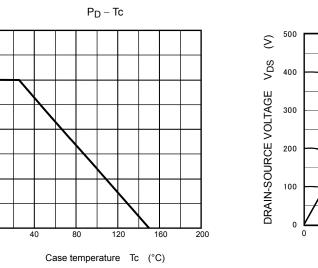
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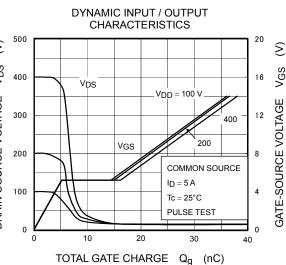
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Drain power dissipation

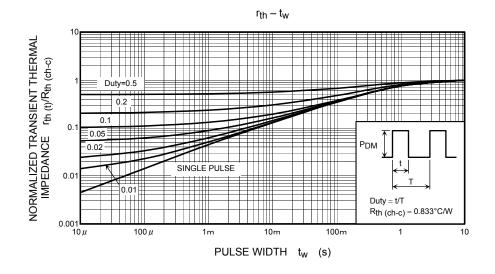


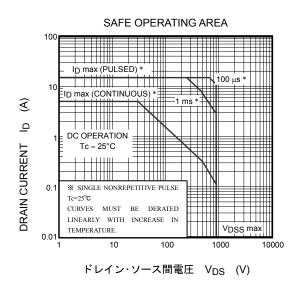


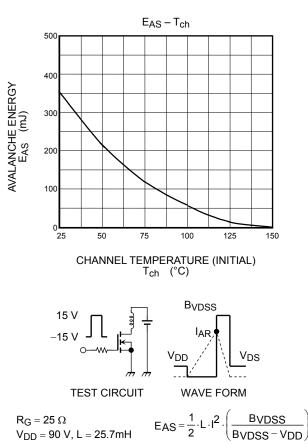


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